NPIC6C596A-Q100

Power logic 8-bit shift register; open-drain outputs

Rev. 2 — 26 June 2020

Product data sheet

1. General description

The NPIC6C596A-Q100 is an 8-bit serial-in/serial or parallel-out shift register with a storage register and open-drain outputs. Both the shift and storage register have separate clocks. The device features a serial input (DS) and a serial output (Q7S) to enable cascading and an asynchronous reset MR input. A LOW on MR resets both the shift register and storage register. Data is shifted on the LOW-to-HIGH transitions of the SHCP input. The data in the shift register is transferred to the storage register on a LOW-to-HIGH transition of the STCP input. If both clocks are connected together, the shift register is always one clock pulse ahead of the storage register. To provide additional hold time in cascaded applications, the serial output QS7 is clocked out on the falling edge of SHCP. Data in the storage register drives the gate of the output extended-drain NMOS (EDNMOS) transistor whenever the output enable input (OE) is LOW. A HIGH on OE causes the outputs to assume a high-impedance OFF-state. Operation of the OE input does not affect the state of the registers. The open-drain outputs are 33 V/100 mA continuous current extended-drain NMOS transistors designed for use in systems that require moderate load power such as LEDs. Integrated voltage clamps in the outputs, provide protection against inductive transients. These voltage clamps make the device suitable for power driver applications such as relays, solenoids and other low-current or medium-voltage loads.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply range 2.3 V to 5.5 V
- Low R_{DSon}
- Eight Power EDNMOS transistor outputs of 100 mA continuous current
- 250 mA current limit capability
- Output clamping voltage 33 V
- · 30 mJ avalanche energy capability
- · Enhanced cascading for multiple stages
- · All registers cleared with single input
- Low power consumption
- ESD protection:
 - HBM AEC-Q100-002 revision D exceeds 2500 V
 - CDM AEC-Q100-011 revision B exceeds 1000 V
- DHVQFN package with Side-Wettable Flanks enabling Automatic Optical Inspection (AOI) of solder joints

3. Applications

- LED sign
- Graphic status panel
- Fault status indicator

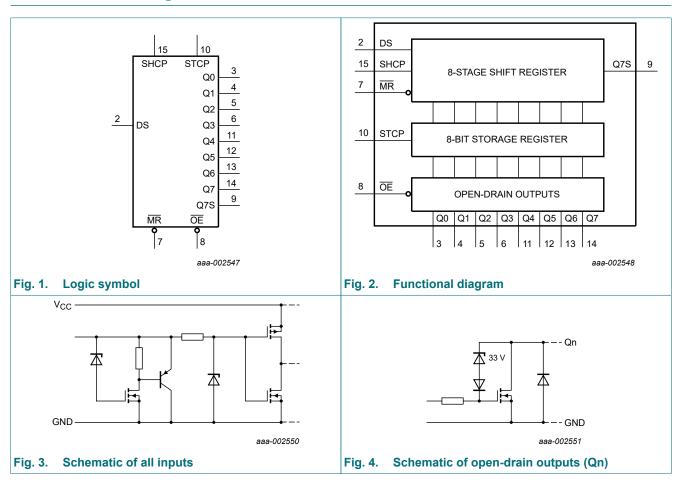


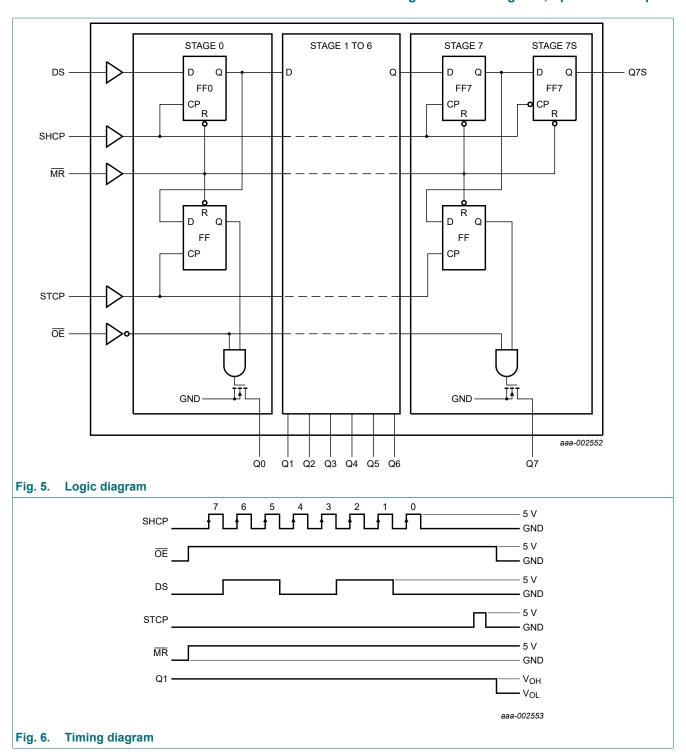
4. Ordering information

Table 1. Ordering information

Type number	Package				
	Temperature range	Name	Description	Version	
NPIC6C596AD-Q100	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1	
NPIC6C596APW-Q100	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1	
NPIC6C596ABQ-Q100	-40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1	

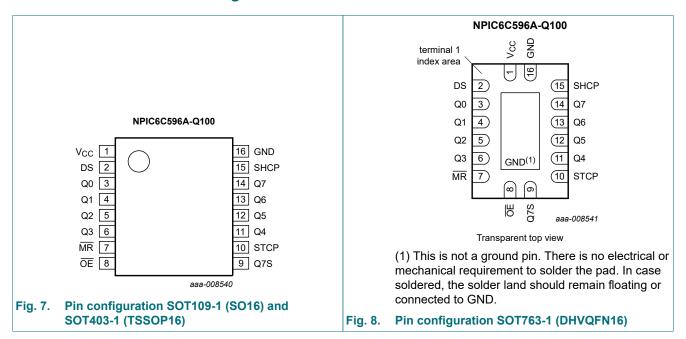
5. Functional diagram





6. Pinning information

6.1. Pinning



6.2. Pin description

Table 2. Pin description

Symbol	Pin	Description
V _{CC}	1	supply voltage
DS	2	serial data input
Q0, Q1, Q2, Q3, Q4, Q5, Q6, Q7	3, 4, 5, 6, 11, 12, 13, 14	parallel data output (open-drain)
MR	7	master reset (active LOW)
ŌĒ	8	output enable input (active LOW)
Q7S	9	serial data output
STCP	10	storage register clock input
SHCP	15	shift register clock input
GND	16	ground (0 V)

7. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+7.0	V
VI	input voltage			-0.3	+7.0	V
V _{DS}	drain-source voltage	power EDNMOS drain-source voltage	[1]	-	+33	V
I _{d(SD)}	source-drain diode current	continuous		-	250	mA
		pulsed	[2]	-	500	mA
I _D	drain current	T _{amb} = 25 °C				
		continuous; each output; all outputs on		-	100	mA
		pulsed; each output; all outputs on	[2]	-	250	mA
I _{DM}	peak drain current	single output; T _{amb} = 25 °C	[2]	-	250	mA
E _{AS}	non-repetitive avalanche energy	single pulse; see Fig. 9	[3]	-	30	mJ
I _{AL}	avalanche current	see Fig. 9	[3]	-	200	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = 25 °C	[4]			
		SO16		-	800	mW
		TSSOP16		-	725	mW
		DHVQFN16		-	1825	mW
		T _{amb} = 125 °C	[4]			
		SO16		-	160	mW
		TSSOP16		-	145	mW
		DHVQFN16		-	365	mW

^[1] Each power EDNMOS source is internally connected to GND.

^[2] Pulse duration ≤ 100 µs and duty cycle ≤ 2 %.

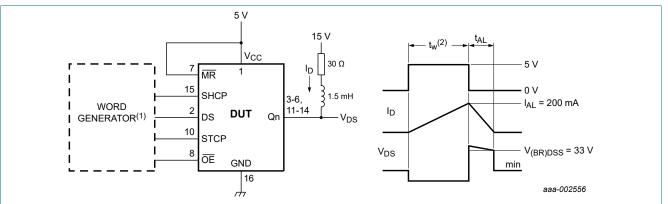
^[3] $V_{DS} = 15 \text{ V}$; starting junction temperature (T_j) = 25 °C; L = 1.5 H; avalanche current (I_{AL}) = 200 mA.

^[4] For SO16 packages: above 25 °C the value of P_{tot} derates linearly with 6.4 mW/°C.

For TSSOP16 packages: above 25 °C the value of P_{tot} derates linearly with 5.8 mW/°C.

For DHVQFN16 packages: above 25 °C the value of Ptot derates linearly with 14.6 mW/°C.

7.1. Test circuit and waveform



- (1) The word generator has the following characteristics: t_r , $t_f \le 10$ ns; $Z_O = 50 \Omega$
- (2) The input pulse duration (t_W) is increased until peak current I_{AL} = 200 mA. Energy test level is defined as: $E_{AS} = I_{AL} \times V_{(BR)DSS} \times t_{AL}/2 = 30$ mJ.

Fig. 9. Test circuit and waveform for measuring single-pulse avalanche energy

8. Recommended operating conditions

Table 4. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		2.3	-	5.5	V
VI	input voltage		0	-	5.5	V
I _D	drain current	pulsed drain output current; $V_{CC} = 5 \text{ V}$; [1] [2] $T_{amb} = 25 \text{ °C}$; all outputs on	-	-	250	mA
T _{amb}	ambient temperature		-40	-	+125	°C

- [1] Pulse duration ≤ 100 µs and duty cycle ≤ 2 %.
- [2] Technique should limit T_i T_{amb} to 10 °C maximum.

9. Static characteristics

Table 5. Static characteristics

At recommended operating conditions unless otherwise specified. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T,	C	Unit	
			Min	Typ [1]	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 3.0 V to 5.5 V	0.85V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 3.0 V to 5.5 V	-	-	0.15V _{CC}	V
V_{OH} HIGH-level output voltage serial data output Q7S; $V_{I} = V_{IH}$ or V_{IL} $I_{O} = -20 \ \mu A; V_{CC} = 3.0 \ V$	serial data output Q7S; V _I = V _{IH} or V _{IL}					
	voltage	I _O = -20 μA; V _{CC} = 3.0 V	2.64	4.49	-	V
		I _O = -4 mA; V _{CC} = 3.0 V	2.4	4.2	-	V
V_{OL}	LOW-level output	serial data output Q7S; V _I = V _{IH} or V _{IL}				
	voltage	I _O = 20 μA; V _{CC} = 3.0 V	-	0.005	0.12	V
		I _O = 4 mA; V _{CC} = 3.0 V	-	0.3	0.6	V
I _I	input leakage current	$V_{CC} = 5.5 \text{ V}; V_I = V_{CC}$	-	-	1	μΑ

Symbol	Parameter	Conditions	Т	_{amb} = 25 °	С	Unit	
			Min	Typ [1]	Max		
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 1 mA	33	37	-	V	
V_{SD}	source-drain voltage	diode forward voltage; I _F = 100 mA	-	- 0.85 1.2			
I _{CC}	supply current	logic supply current; $V_{CC} = 5.5 \text{ V}$; $V_{I} = V_{CC}$ or GND					
		all outputs off	-	0.004	200	μA	
		all outputs on [2]	-	0.006	500	μA	
		all outputs off; SHCP = 5 MHz; C_L = 30 pF; see Fig. 14 and Fig. 16	-	0.75	5	mA	
$I_{O(nom)}$	nominal output current	$V_{DS} = 0.5 \text{ V}; T_{amb} = 85 \text{ °C}; I_{out} = I_{D}$ [3] [4] [5]	-	140	-	mA	
I _{DSX}	drain cut-off	V _{CC} = 5.5 V; V _{DS} = 30 V	-	0.002	0.2	μA	
	current	V _{CC} = 5.5 V; V _{DS} = 30 V; T _{amb} = 125 °C	-	0.15	0.3	μΑ	
R _{DSon}	drain-source	see <u>Fig. 17</u> and <u>Fig. 18</u> [3] [4]					
	on-state resistance	V _{CC} = 3.0 V; I _D = 50 mA	-	3.0	11	Ω	
	i Coloralio C	V _{CC} = 3.0 V; I _D = 50 mA; T _{amb} = 125 °C		5.4	14	Ω	
		V _{CC} = 3.0 V; I _D = 100 mA	-	3.1	12	Ω	

- Typical values are measured at T_{amb} = 25 °C and V_{CC} = 5.0 V. Output currents below 250 mA current limit.
- [2] [3]
- Technique should limit T_j T_{amb} to 10 °C maximum. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
- Nominal output current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at T_{amb} = 85 °C.

10. Dynamic characteristics

Table 6. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); For test circuit, see Figure 14.

Symbol	Parameter	Conditions		Т	amb = 25 °	С	Unit
			Min	Typ [1]	Max		
t _{PLH}	LOW to HIGH propagation delay	\overline{OE} to Qn; I _D = 75 mA; see Fig. 10 and Fig. 19		-	97	-	ns
t _{PHL}	HIGH to LOW propagation delay	$\overline{\text{OE}}$ to Qn; I _D = 75 mA; see Fig. 10 and Fig. 19		-	9	-	ns
t _r	rise time	$\overline{\text{OE}}$ to Qn; I _D = 75 mA; see <u>Fig. 10</u> and <u>Fig. 19</u>		-	60	-	ns
t _f	fall time	$\overline{\text{OE}}$ to Qn; I _D = 75 mA; see <u>Fig. 10</u> and <u>Fig. 19</u>		-	18	-	ns
t _{pd}	propagation delay	SHCP to Q7S; I _D = 75 mA; see Fig. 11	[2]	-	5	-	ns
f _{max}	maximum frequency	SHCP; I _D = 75 mA; see <u>Fig. 11</u>	[3]	-	-	10	MHz
t _{rr}	reverse recovery time	I _F = 100 mA; dI/dt = 10 A/μs; see <u>Fig. 13</u>	[4] [5]	-	120	-	ns
t _a	reverse recovery current rise time	$I_F = 100 \text{ mA}$; dl/dt = 10 A/ μ s; see Fig. 13	[4] [5]	-	100	-	ns
t _{su}	set-up time	DS to SHCP; see Fig. 12		15	-	-	ns
t _h	hold time	DS to SHCP; see Fig. 12		15	-	-	ns
t _W	pulse width			40	-	-	ns

- [1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 5.0 V.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] This is the maximum serial clock frequency assuming cascaded operation where serial data is passed from one stage to a second stage. The clock period allows for SHCP → Q7S propagation delay and setup time plus some timing margin.
- [4] Technique should limit T_j T_{amb} to 10 °C maximum.
- [5] These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

10.1. Test circuits and waveforms

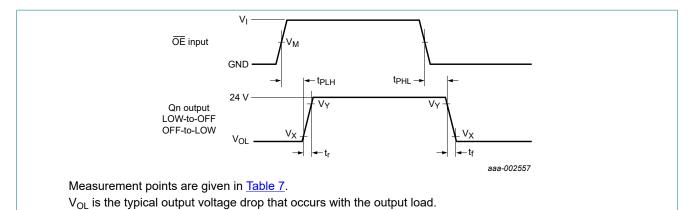
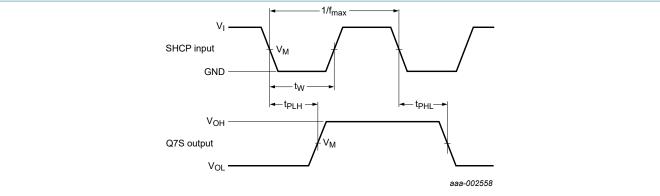


Fig. 10. The output enable (OE) input to data output (Qn) propagation delays and (Qn) output rise and fall times



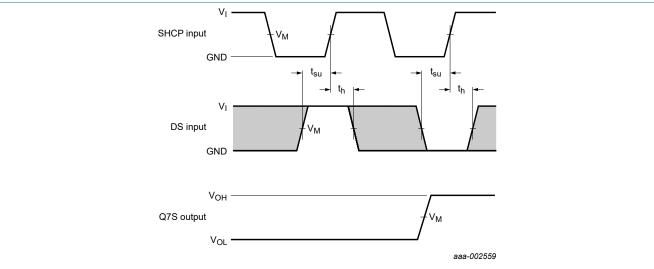
Measurement points are given in <u>Table 7</u>.

 V_{OL} and V_{OH} are the typical output voltage levels that occur with the output load.

Fig. 11. The shift clock (SHCP) to serial data output (Q7S) propagation delays with the minimum shift clock pulse width and maximum shift clock frequency

Table 7. Measurement points

	Supply voltage	Input	Output					
V _{cc}		V _M	V _M	V _X	V _Y			
	5 V	0.5V _{CC}	0.5V _{DS}	0.1V _{DS}	0.9V _{DS}			



Measurement points are given in <u>Table 8</u>.

The shaded areas indicate when the input is permitted to change for predictable output performance.

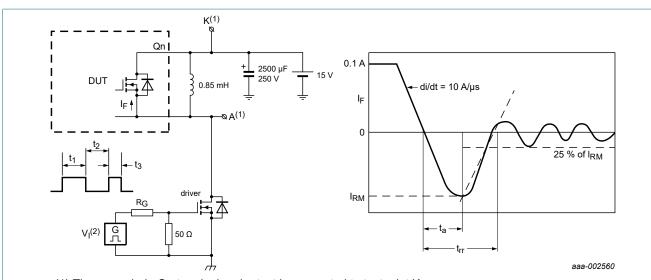
 V_{OL} and V_{OH} are the typical output voltage levels that occur with the output load.

Fig. 12. The data set-up and hold times for the serial data input (DS)

Table 8. Measurement points

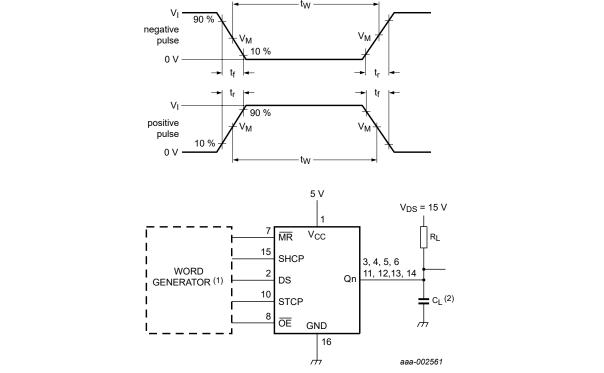
Supply voltage	Input Output			
V _{CC}	V _M	V _M		
5 V	0.5V _{CC}	0.5V _{CC}		

Product data sheet



- (1) The open-drain Qn terminal under test is connected to testpoint K. All other terminals are connected together and connected to testpoint A.
- (2) The V_I amplitude and R_G are adjusted for dI/dt = 10 A/ μ s. A V_I double-pulse train is used to set I_F = 0.1 A, where t₁ = 10 μ s, t₂ = 7 μ s and t₃ = 3 μ s.

Fig. 13. Test circuit and waveform for measuring reverse recovery current



(1) The word generator has the following characteristics:

 t_r , $t_f \le 10 \text{ ns}$;

 $t_W = 300 \text{ ns};$

pulsed repetition rate (PRR) = 5 kHz;

 $Z_{\rm O}$ = 50 Ω

(2) C_L includes probe and jig capacitance.

Test data is given in <u>Table 9</u>. Definitions for test circuit:

 V_{DS} = External voltage for Power EDNMOS drain-source voltage.

 R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

Fig. 14. Test circuit for measuring switching times

Table 9. Test data

Supply voltage	Input		Load		
	V_l t_r, t_f V		V _M	CL	R_L
5 V	5 V	≤ 10 ns	50%	30 pF	200 Ω

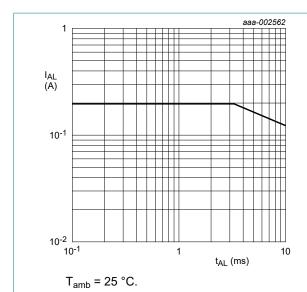


Fig. 15. Avalanche current (peak) versus time duration of avalanche

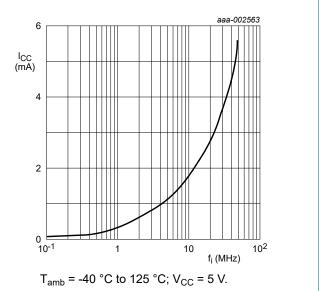
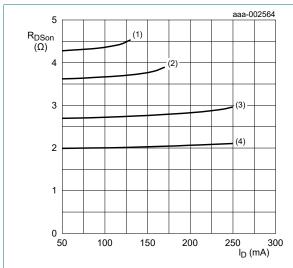


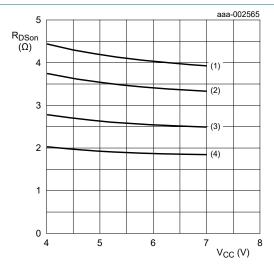
Fig. 16. Supply current versus frequency



 $V_I = V_{CC}$ or GND and $V_O = GND$ or V_{CC} .

- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) T_{amb} = 85 °C
- (3) T_{amb} = 25 °C
- (4) $T_{amb} = -40 \, ^{\circ}C$

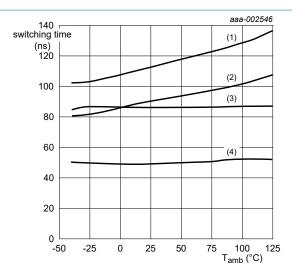
Fig. 17. Drain-source on-state resistance versus drain current



 $V_I = V_{CC}$ or GND and $V_O =$ open circuit.

- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) T_{amb} = 85 °C
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

Fig. 18. Static drain-source on-state resistance versus supply voltage

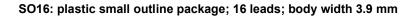


Technique should limit T_J - T_C to 10 $^{\circ}C$ maximum.

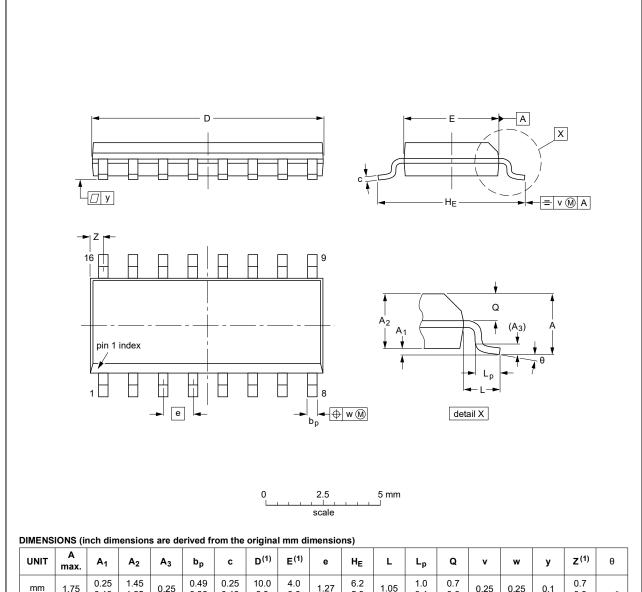
- (1) t_{PLH}.
- (2) t_r.
- (3) t_f.
- (4) t_{PHL}.

Fig. 19. Switching time versus case temperature

11. Package outline



SOT109-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	0°

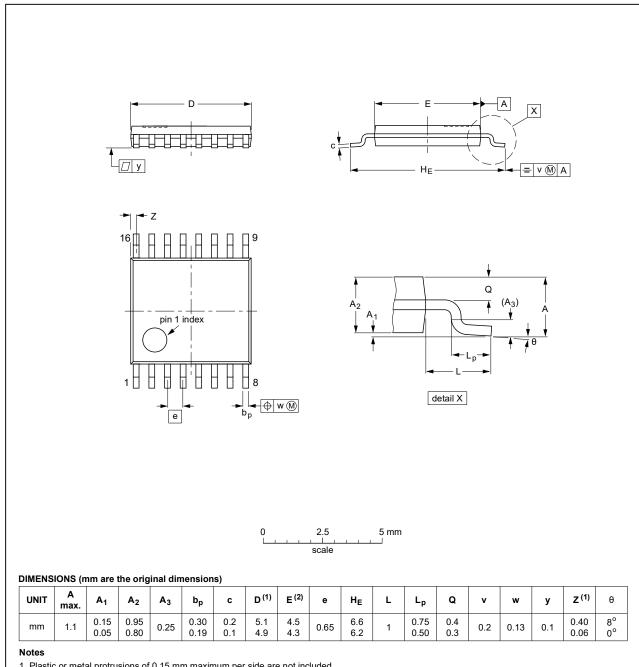
1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT109-1	076E07	MS-012				99-12-27 03-02-19

Fig. 20. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE
	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT403-1		MO-153				99-12-27 03-02-18

Fig. 21. Package outline SOT403-1 (TSSOP16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

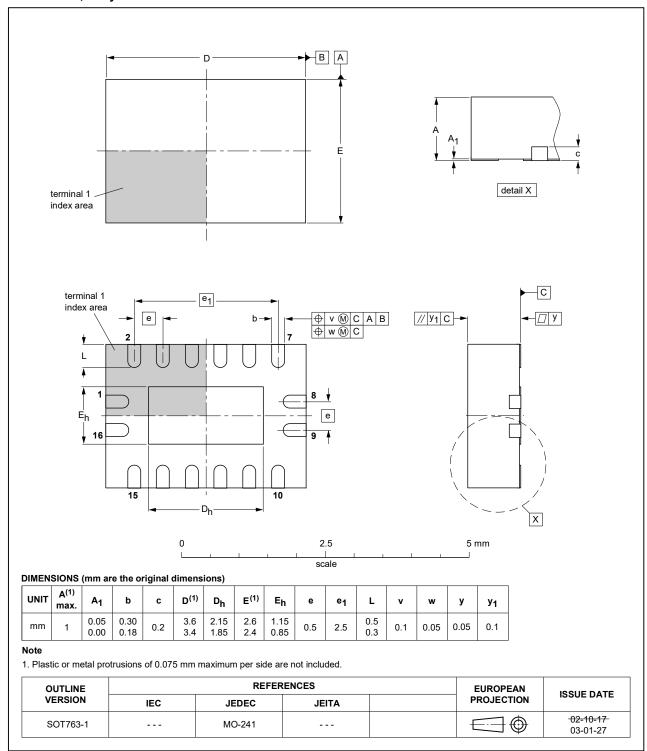


Fig. 22. Package outline SOT763-1 (DHVQFN16)

12. Abbreviations

Table 10. Abbreviations

Table 1417 toble 14410110				
Acronym	Description			
CDM	Charged Device Model			
CMOS	Complementary Metal Oxide Semiconductor			
DUT	Device Under Test			
EDNMOS	Extended Drain Negative Metal Oxide Semiconductor			
ESD	ElectroStatic Discharge			
НВМ	Human Body Model			
TTL	Transistor-Transistor Logic			

13. Revision history

Table 11. Revision history

Table 11. Novicion motory						
Document ID	Release date	Data sheet status	Change notice	Supersedes		
NPIC6C596A_Q100 v.2	20200626	Product data sheet	-	NPIC6C596A_Q100 v.1		
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section 2 updated. 					
NPIC6C596A_Q100 v.1	20131018	Product data sheet	-	-		

14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Power logic 8-bit shift register; open-drain outputs

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 26 June 2020

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